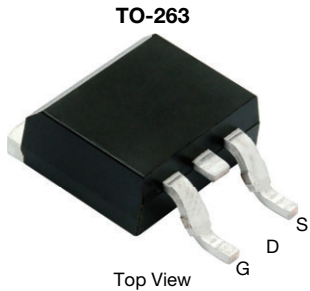


N-Channel 200 V (D-S) MOSFET



PRODUCT SUMMARY	
V_{DS} (V)	200
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0114
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5$ V	0.0129
Q_g typ. (nC)	56.7
I_D (A)	150 ^d
Configuration	Single

FEATURES

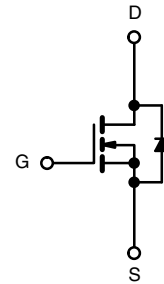
- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature
- Very low Q_{gd} reduces power loss from passing through $V_{plateau}$
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Switching power supply
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management
- OR-ing / e-fuse



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and halogen-free	SUM90100E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V_{DS}	200	V	
Gate-source voltage	V_{GS}	± 20		
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	150 ^d	A	
	$T_C = 70$ °C	150 ^d		
Pulsed drain current ($t = 100$ μ s)	I_{DM}	250		
Avalanche current	I_{AS}	70		
Single avalanche energy ^a	$L = 0.1$ mH	E_{AS}	245	mJ
Maximum power dissipation ^a	$T_C = 25$ °C	P_D	375 ^b	W
	$T_C = 125$ °C		125 ^b	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175		°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient (PCB mount) ^c	R_{thJA}	40	°C/W
Junction-to-case (drain)	R_{thJC}	0.4	

Notes

- Duty cycle ≤ 1 %
- See SOA curve for voltage derating
- When mounted on 1" square PCB (FR4 material)
- Package limited



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	200	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 250	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C	-	-	150	
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 175 °C	-	-	5	mA
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	120	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 16 A	-	0.0095	0.0114	Ω
		V _{GS} = 7.5 V, I _D = 13 A	-	0.0099	0.0129	
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 13 A	-	85	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz	-	3930	-	pF
Output capacitance	C _{oss}		-	450	-	
Reverse transfer capacitance	C _{rss}		-	12	-	
Total gate charge ^c	Q _g	V _{DS} = 100 V, V _{GS} = 10 V, I _D = 16 A	-	72.8	110	nC
Gate-source charge ^c	Q _{gs}		-	19.4	-	
Gate-drain charge ^c	Q _{gd}		-	19.0	-	
Gate resistance	R _g	f = 1 MHz	0.7	3.5	7.0	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 80 V, R _L = 6.2 Ω I _D ≅ 13 A, V _{GEN} = 10 V, R _g = 1 Ω	-	20	40	ns
Rise time ^c	t _r		-	50	100	
Turn-off delay time ^c	t _{d(off)}		-	60	120	
Fall time ^c	t _f		-	18	36	
Drain-Source Body Diode Ratings and Characteristics ^b (T_C = 25 °C)						
Pulsed current (t = 100 μs)	I _{SM}		-	-	250	A
Forward voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V	-	0.8	1.5	V
Reverse recovery time	t _{rr}	I _F = 13 A, di/dt = 100 A/μs	-	118	177	ns
Peak reverse recovery charge	I _{RM(REC)}		-	9.4	14.1	A
Reverse recovery charge	Q _{rr}		-	0.632	0.948	μC
Reverse recovery fall time	t _a		-	94	-	ns
Reverse recovery rise time	t _b		-	24	-	

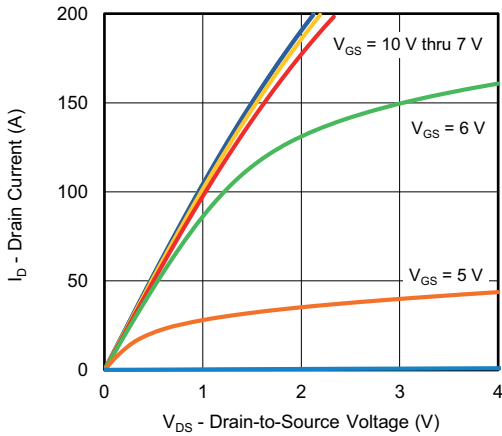
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

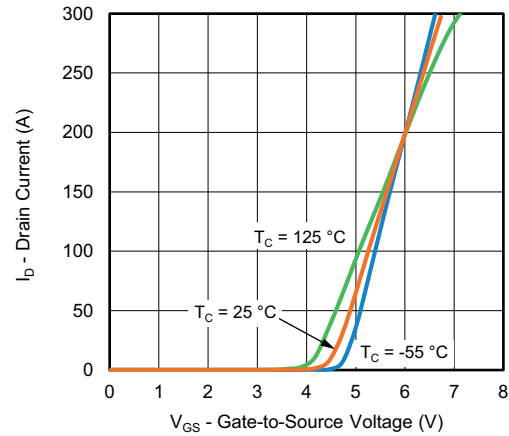
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



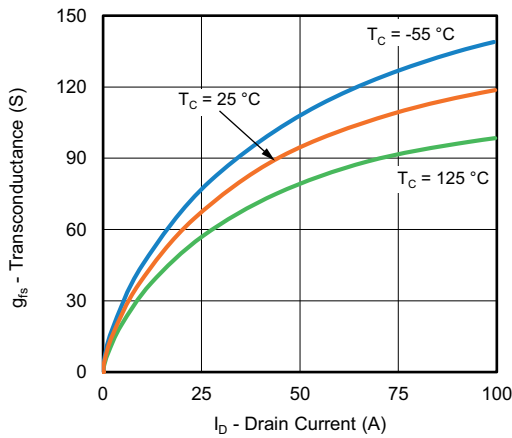
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



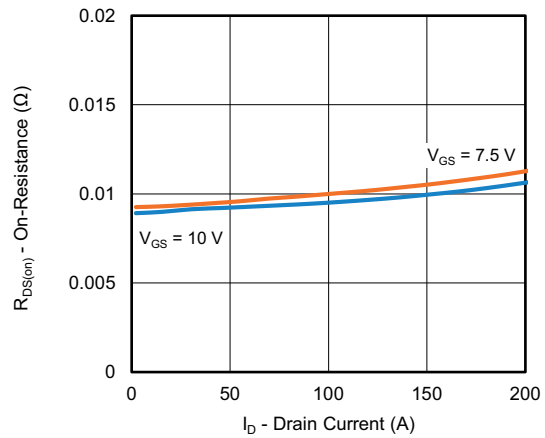
Output Characteristics



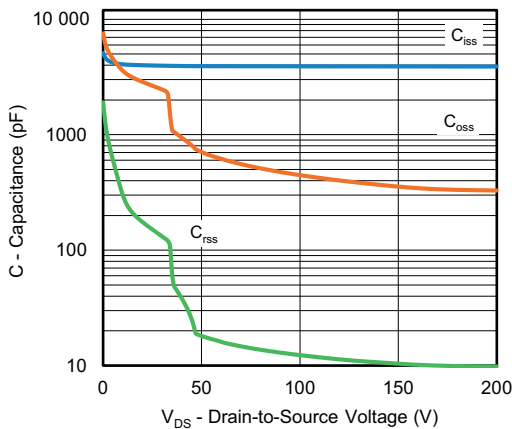
Transfer Characteristics



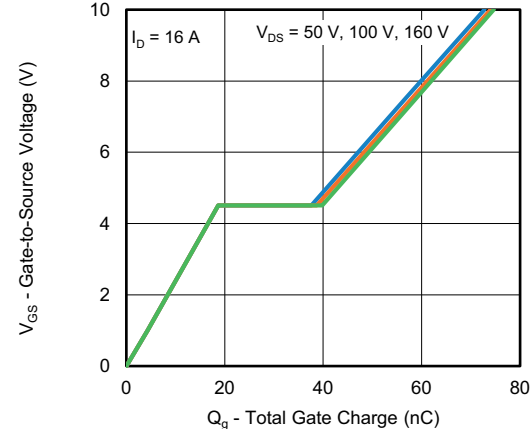
Transconductance



On-Resistance vs. Drain Current



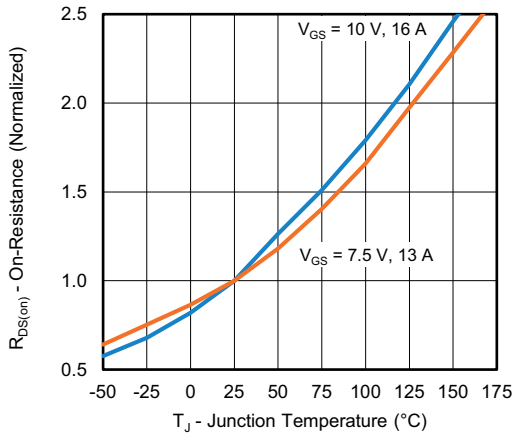
Capacitance



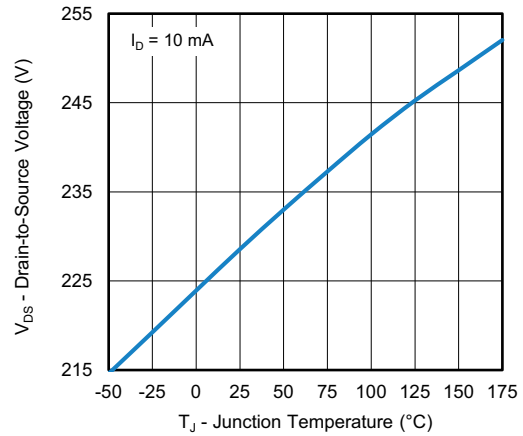
Gate Charge



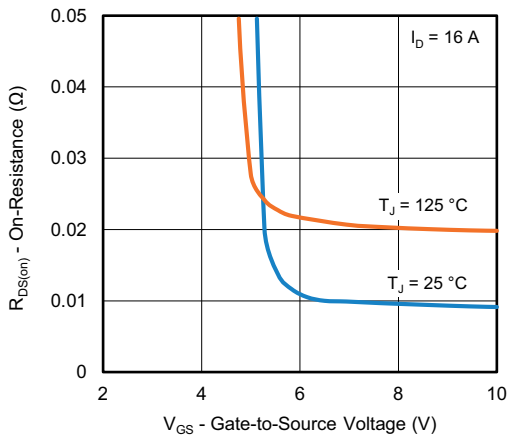
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



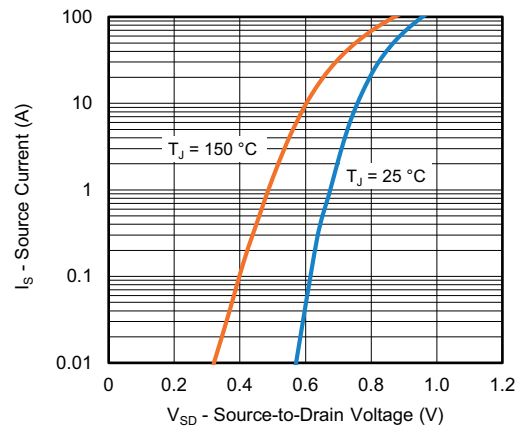
On-Resistance vs. Junction Temperature



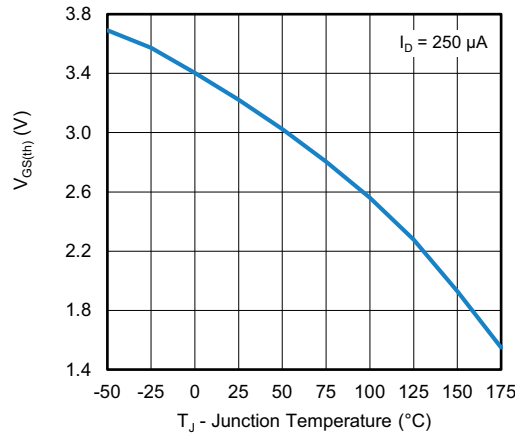
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



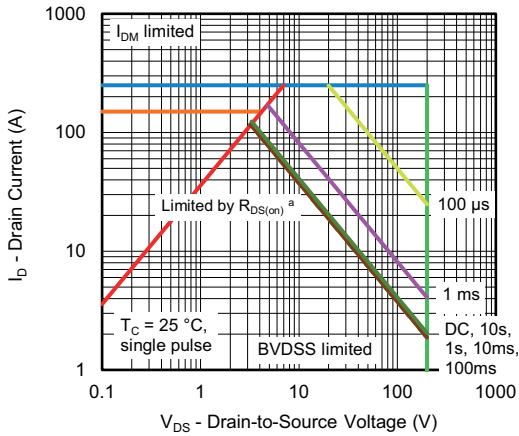
Source Drain Diode Forward Voltage



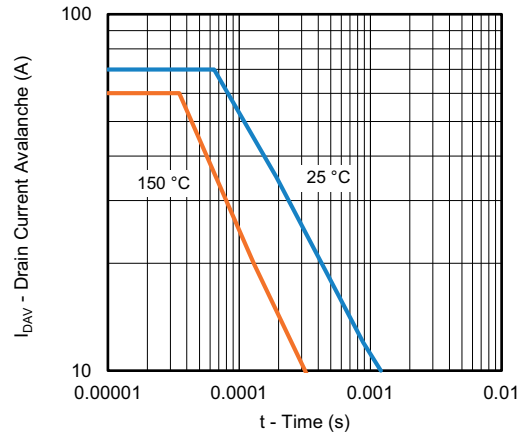
Threshold Voltage



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



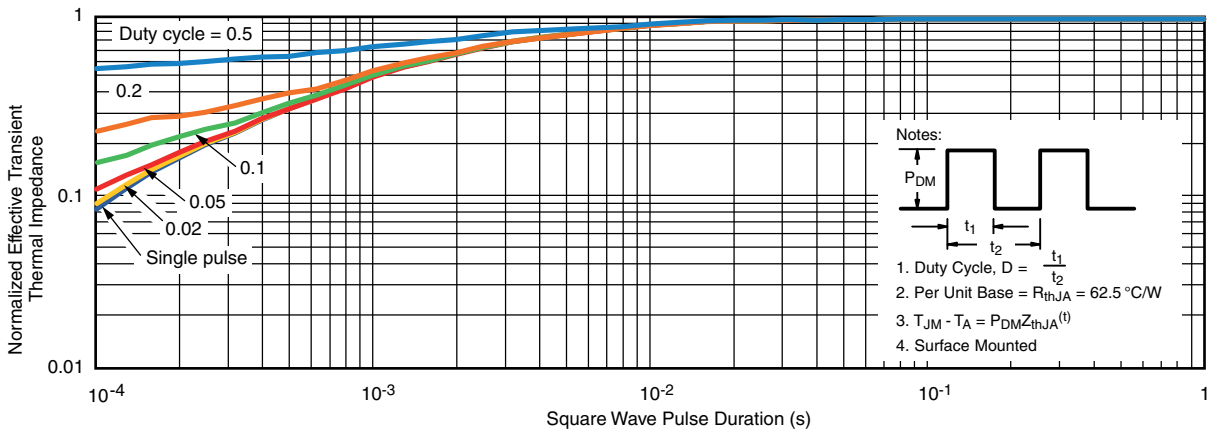
Safe Operating Area



Single Pulse Avalanche Current Capability vs. Time

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-263 (D²PAK): 3-LEAD



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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